

<b>SANYO</b>	No.3449A	<b>2SK1446</b>
		N-Channel Silicon MOSFET Ultrahigh-Speed Switching Applications

**Features**

- Low ON-state resistance.
- Ultrahigh-speed switching.
- Micaless package facilitating easy mounting.

**Absolute Maximum Ratings at Ta = 25°C**

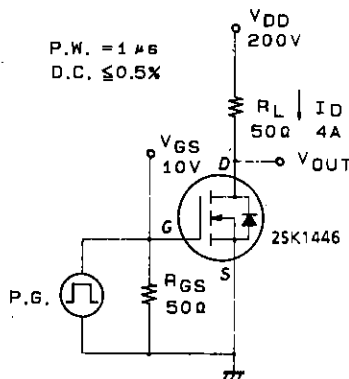
			unit
Drain-to-Source Voltage	V <sub>DS</sub>	450	V
Gate-to-Source Voltage	V <sub>GS</sub>	±30	V
Drain Current(DC)	I <sub>D</sub>	7	A
Drain Current(Pulse)	I <sub>DP</sub>	PW ≤ 10μs, duty cycle ≤ 1%	28 A
Allowable Power Dissipation	P <sub>D</sub>	2.0	W
		Tc = 25°C	35 W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C

**Electrical Characteristics at Ta = 25°C**

			min	typ	max	unit
D-S Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 1mA, V <sub>GS</sub> = 0	450			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 450V, V <sub>GS</sub> = 0			1.0	mA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±30V, V <sub>DS</sub> = 0			±100	nA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA	2.0		3.0	V
Forward Transfer Admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 4A	3.0	6.0		S
Static Drain-to-Source ON-State Resistance	R <sub>DS(on)</sub>	I <sub>D</sub> = 4A, V <sub>GS</sub> = 10V		0.6	0.8	Ω
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 20V, f = 1MHz		1200		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 20V, f = 1MHz		180		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> = 20V, f = 1MHz		70		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	I <sub>D</sub> = 4A, V <sub>GS</sub> = 10V V <sub>DD</sub> = 200V, R <sub>GS</sub> = 50Ω		20		ns
Rise Time	t <sub>r</sub>		40		ns	
Turn-OFF Delay Time	t <sub>d(off)</sub>		160		ns	
Fall Time	t <sub>f</sub>		60		ns	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 7A, V <sub>GS</sub> = 0			1.8	V

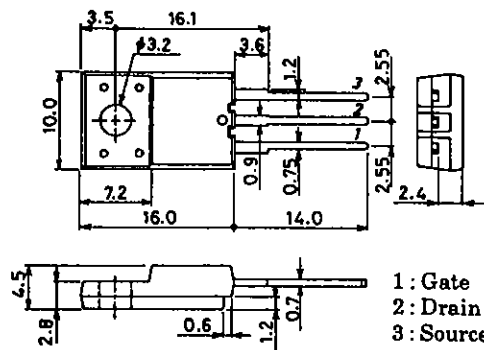
(Note) Be careful in handling the 2SK1446 because it has no protection diode between gate and source.

**Switching Time Test Circuit**



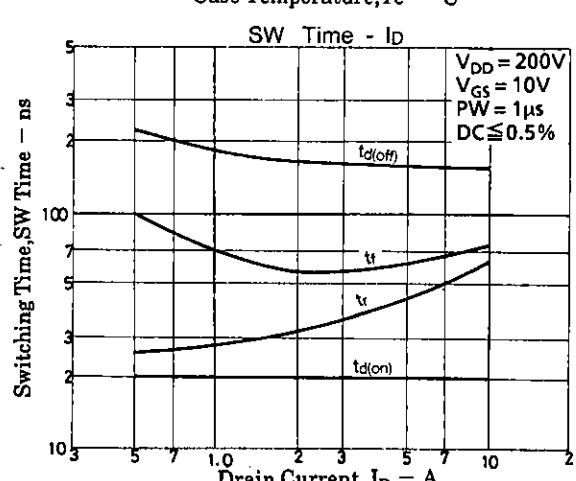
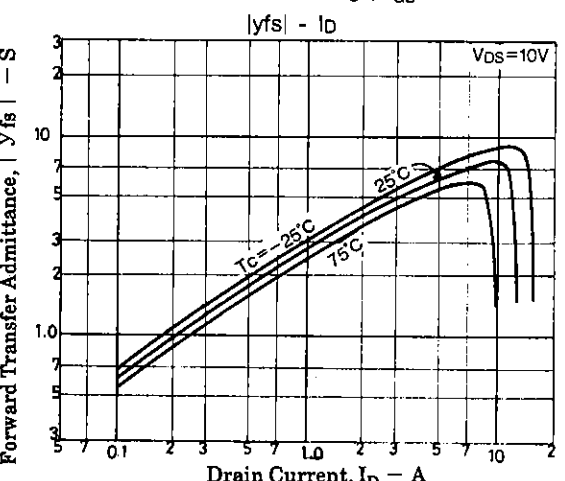
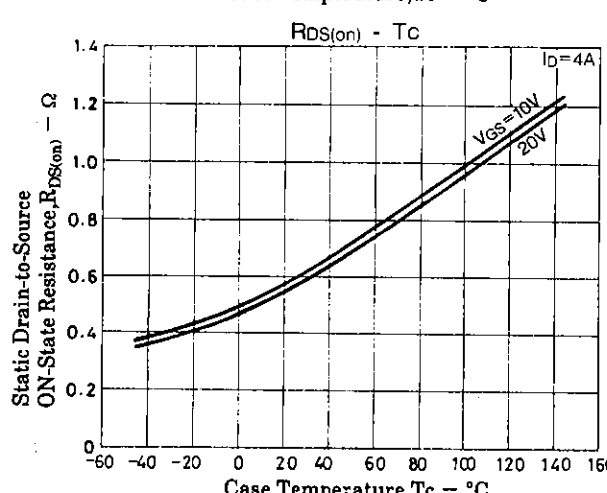
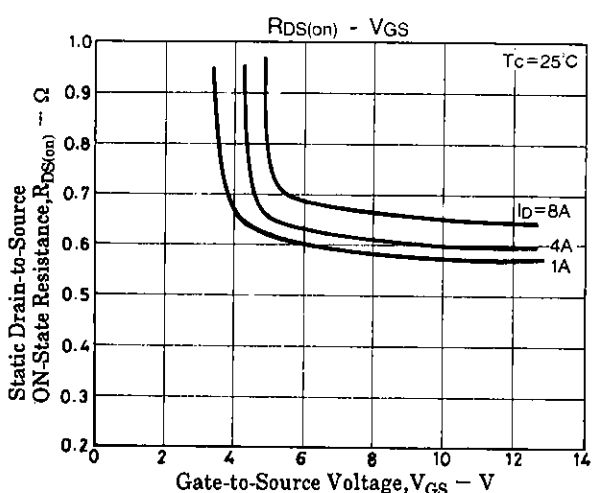
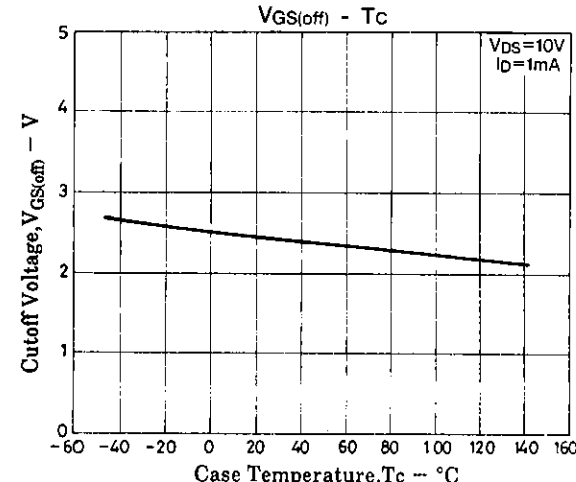
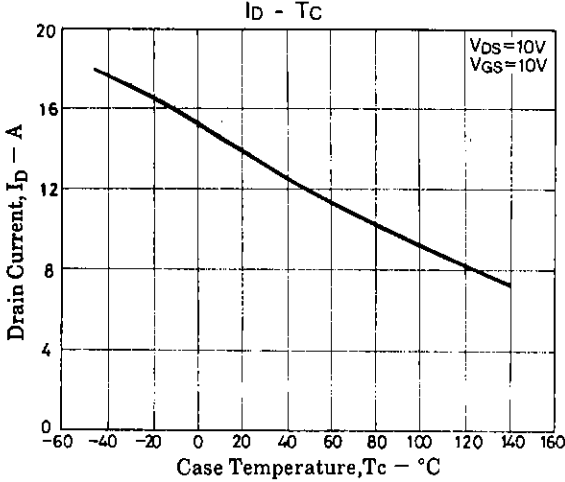
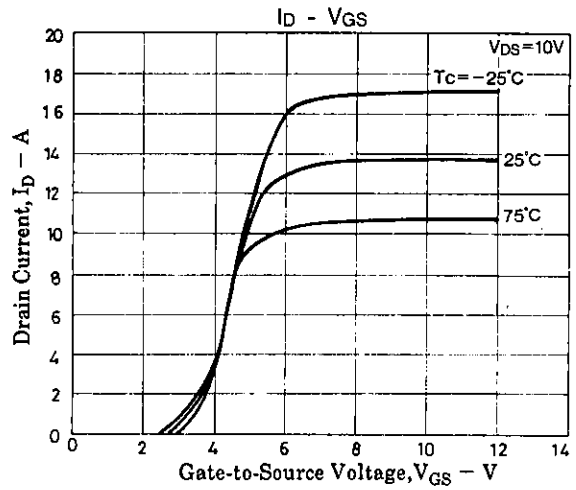
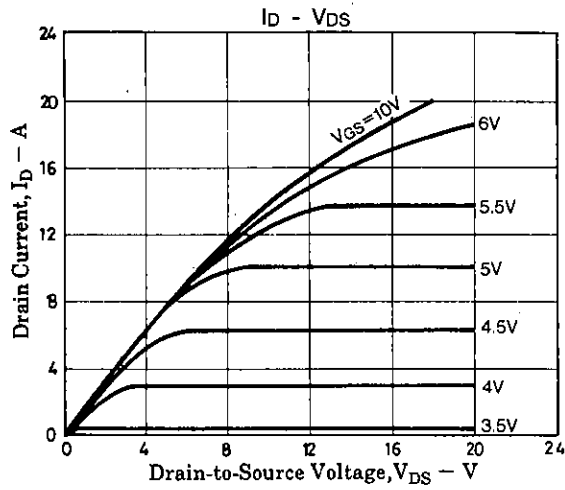
**Package Dimensions 2078B**

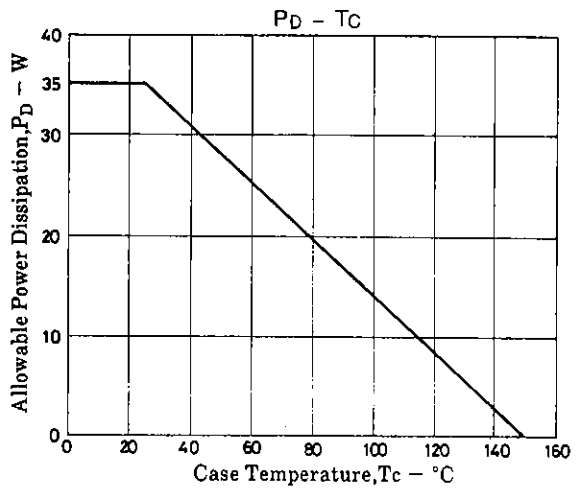
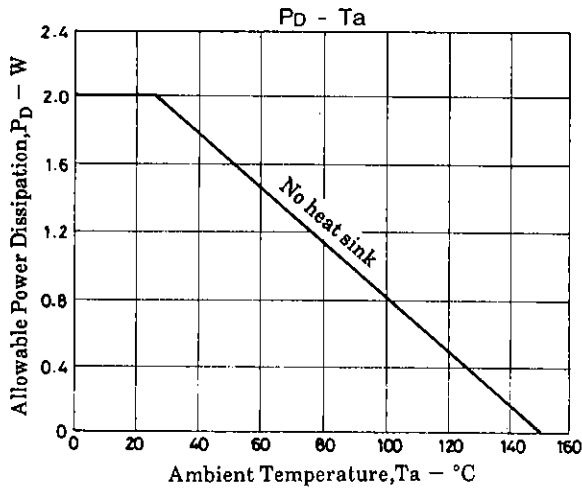
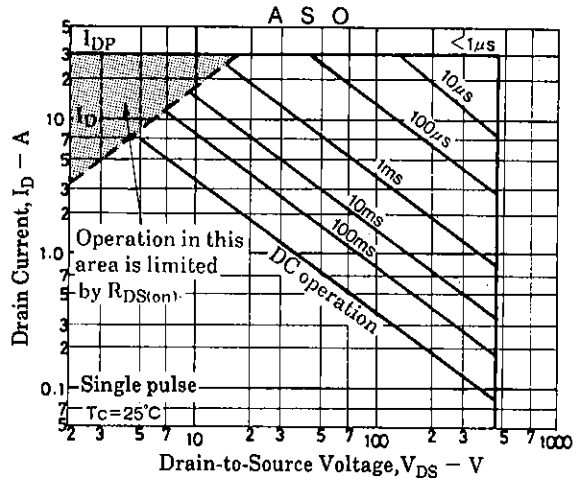
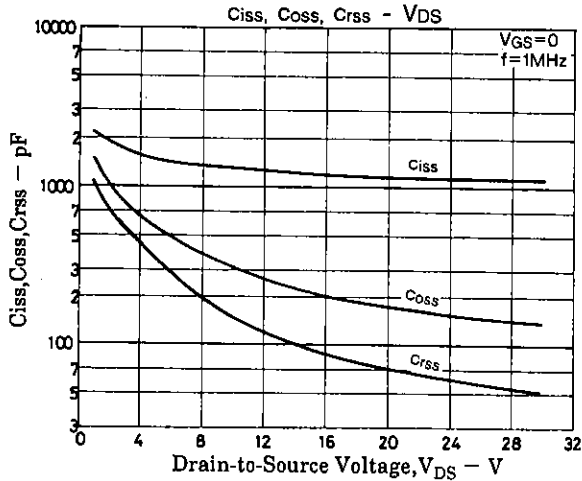
(unit : mm)



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